



**TET ESTEL AS
ESTONIA**

**January
2016**

**Series
D243-1000**

**Rectifier Press-Pack
Diode
Type D243-1000**

Designed for rectifiers and industrial applications

Maximum mean forward current	I _{FAV}	1000 A
Maximum repetitive peak reverse voltage	U _{RRM}	1600 ÷ 2800 V
Reverse recovery time	trr (typ)	35 µs
U _{RRM} , V	1600	1800
Voltage code	16	18
Tvj, °C	- 60 ÷ 175	

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	D243-1000	Conditions
I _{FAV}	Mean forward current	A	1000 1870	Tc=127 °C Tc=55 °C, 180° half-sine wave, 50 Hz
I _{FRMS}	RMS forward current	A	1570	Tc=127 °C
I _{FSM}	Surge forward current	kA	17 19	Tvj=175°C Tvj=25°C
I ² t	Limiting load integral	kA ² s	1445 1805	Tvj=175°C Tvj=25°C tp=10 ms UR=0
U _{RRM}	Repetitive peak reverse voltage	V	1600÷2800	Tj min≤Tvj≤TjM 180° half-sine wave, 50 Hz
U _{RSR}	Non-repetitive peak reverse voltage	V	1700÷2900	Tj min≤Tvj≤TjM 180° half-sine wave tp=10 ms, Single pulse
T _{stg}	Storage temperature	°C	-60÷80	
Tvj	Junction temperature	°C	-60÷175	

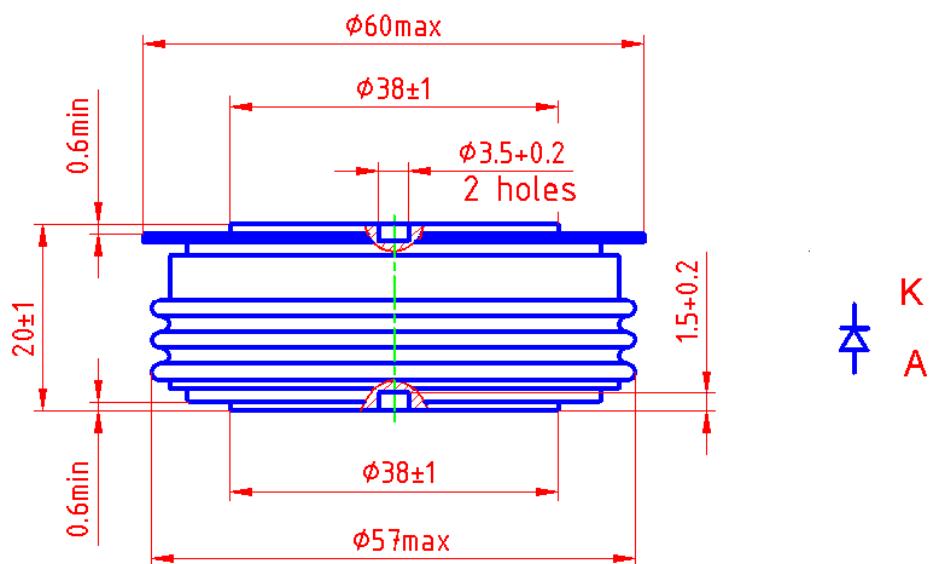
CHARACTERISTICS

U _{FM}	Peak forward voltage	V	1,7	Tvj=25°C, ITM=3,14 ITAV
U _{F(TO)}	Threshold voltage	V	0,9	Tvj=175°C 1,57 ITAV < IT < 4,71 ITAV
R _T	Forward slope resistance	mΩ	0,27	
I _{RRM}	Repetitive peak reverse current	mA	50	Tvj=175°C, UR= U _{RRM}

CHARACTERISTICS				
Symbols and parameters		Units	D243-1000	Conditions
Qrr	Recovered charge (typ)	μC	2700	Tvj=175°C If=1000 A diR/dt =10 A/ μs UR=100V
trr	Reverse recovery time (typ)	μs	35	
IrrM	Peak reverse recovery current (typ)	A	155	
Rthjc	Thermal resistance junction to case	$^{\circ}\text{C}/\text{W}$	0,03	
				Direct current, double side cooled

ORDERING				
	D	243	1000	24
	1	2	3	4

1. Diode
2. Design version
3. Mean forward current, A
4. Voltage code (24=2400 V)



Mounting force : 13 ÷ 19 kN
Weight : 260 grams